

Features

- Advanced trench process technology
- Extremely low on-resistance $R_{DS(on)}$
- High Ruggedness
- 100% Avalanche Tested

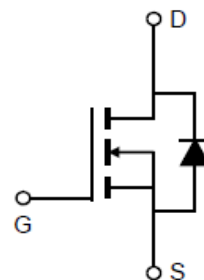
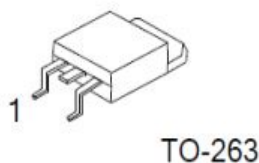
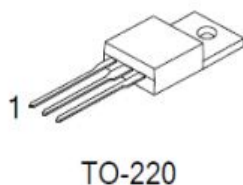
Application

- Power Management in inverter System
- Synchronous Rectification

Product Summary

V _{DS}	120V
$R_{DS(on)}@V_{GS}=10V$	8.0 mΩ
I _D	120A

Part ID	Package Type	Marking
SFP120N120	TO-220	120N120
SFB120N120	TO-263	120N120



Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	120	V
Continuous drain current T _C = 25°C (Package limit) T _C = 100°C (Package limit)	I _D	120 90	A
Pulsed drain current T _C = 25°C, t _p limited by T _{jmax}	I _{D pulse}	480	
Avalanche energy, single pulse (L=0.033mH, V _{DS} =80V)	E _{AS}	600	mJ
Gate-emitter voltage	V _{GS}	±20	V
Power dissipation T _C = 25°C	P _{tot}	230	W
Operating junction and storage temperature	T _j , T _{stg}	-55...+150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R _{thJC}	0.55	°C/W
Thermal resistance, junction – ambient. Max	R _{thJA}	62.0	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Test Condition	Value			Unit
			min.	typ.	max.	

Static Characteristic

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	120	128	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$	2.0 -	3	4.0 -	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$	- -	0.05	1 5	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=50A,$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$	- -	6.2	8.0 -	m Ω
Transconductance	g_{fs}	$V_{DS}=50V, I_D=20A$	-	36	-	S

Dynamic Characteristic

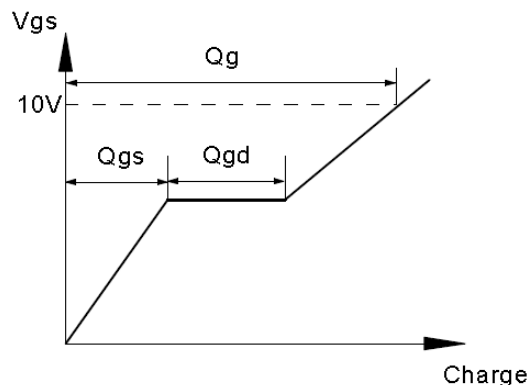
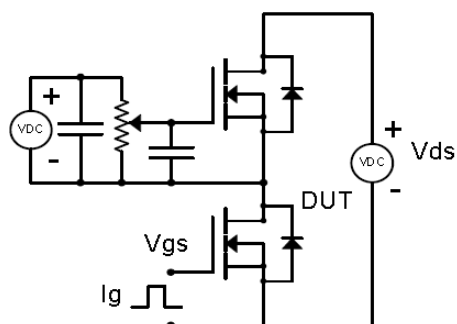
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=50V,$ $f=1\text{MHz}$	-	9500	-	pF
Output Capacitance	C_{oss}		-	1467	-	
Reverse Transfer Capacitance	C_{rss}		-	62	-	
Gate Total Charge	Q_G	$V_{GS}=10V, V_{DS}=50V,$ $I_D=20A, f=1\text{MHz}$	-	165	-	nC
Gate-Source charge	Q_{gs}		-	63	-	
Gate-Drain charge	Q_{gd}		-	54	-	
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}, V_{GS}=10V,$ $V_{DS}=50V, R_L=2.5\Omega$		62		ns
Rise time	t_r			73		
Turn-off delay time	$t_{d(off)}$			87		
Fall time	t_f			41		
Gate resistance	R_G	$V_{GS}=0V, V_{DS}=0V,$ $f=1\text{MHz}$	-	1.7	-	Ω

Body Diode Characteristic

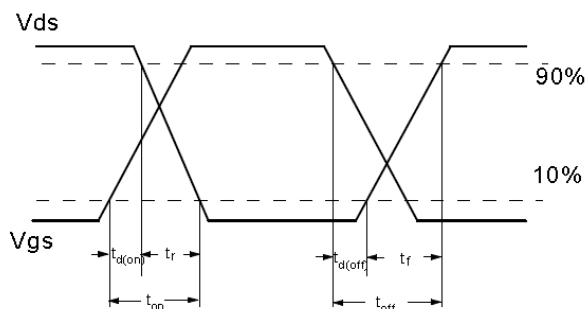
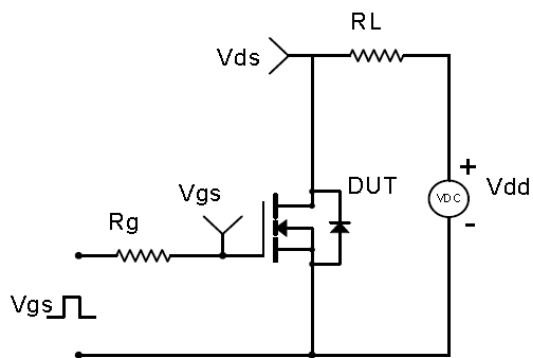
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=50A$	-	0.85	1.3	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=20A,$ $dI/dt=500A/\mu s$		60		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F=20A,$ $dI/dt=500A/\mu s$		560		nC

Test Circuit & Waveform

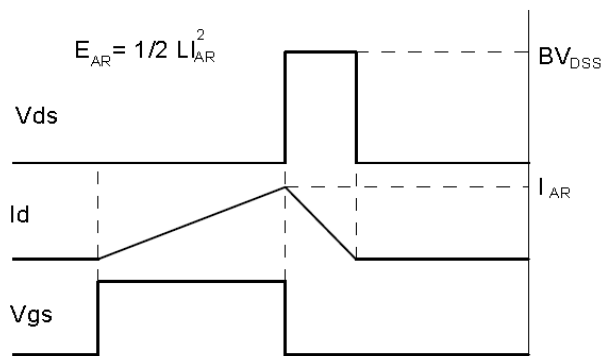
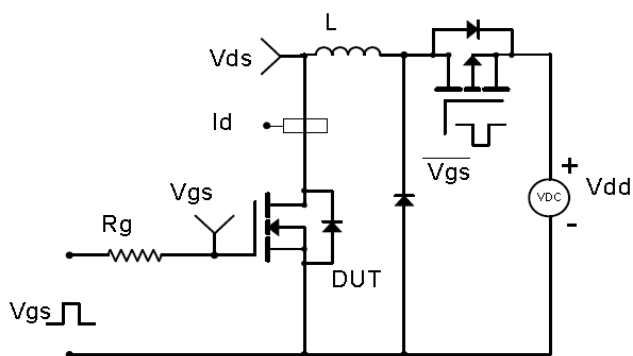
Gate Charge Test Circuit & Waveform



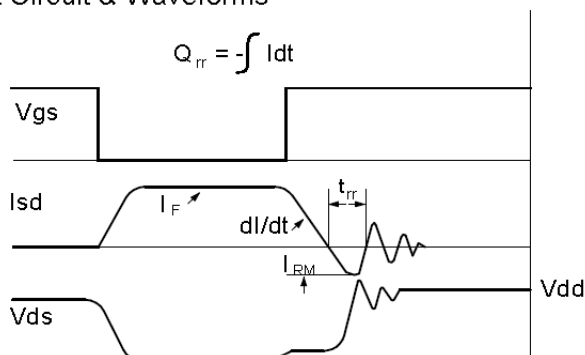
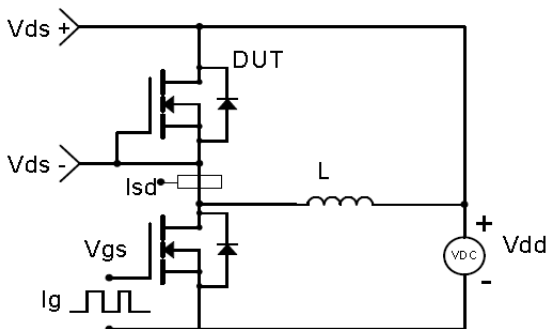
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

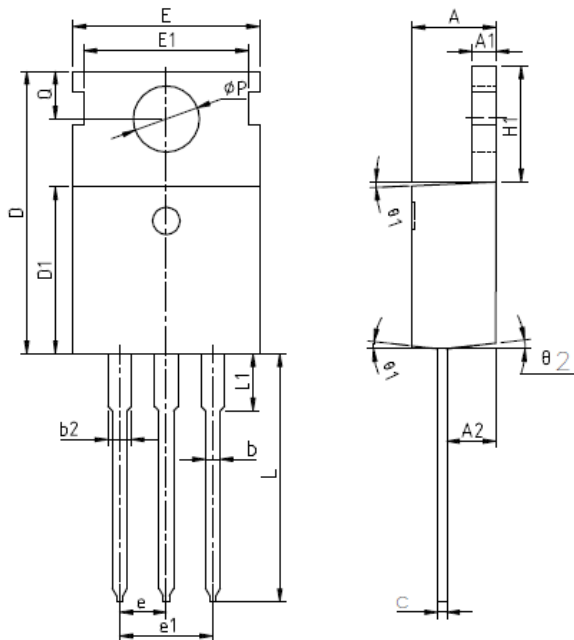


Diode Recovery Test Circuit & Waveforms



PACKAGE DIMENSION

TO-220



SYMBOL	MIN	NOM	MAX
A	4.27	4.57	4.87
A1	1.15	1.30	1.45
A2	2.10	2.40	2.70
b	0.70	0.80	1.00
b2	1.17	1.27	1.50
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.70	6.70	7.00
E	9.70	10.00	10.30
E1	-	8.70	-
E2	9.65	10.00	10.35
E3	7.00	8.00	8.40
e	2.54 BSC		
e1	5.08 BSC		
H1	6.00	6.50	6.85
L	12.75	13.50	13.90
L1	-	3.10	3.40
ϕP	3.45	3.60	3.75
Q	2.60	2.80	3.00
$\theta 1$	4°	7°	10°
$\theta 2$	0°	3°	6°

TO-263

